

ALTERNATIVE TO PTO/SB/08A/B
(Based on PTO 09-09 version)

Substitute for form 1449/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	10/514,429	
			Filing Date	July 12, 2005	
			First Named Inventor	Robert DWILINSKI	
			Art Unit	2881	
			Examiner Name	M. J. Logie	
Sheet	1	of	3	Attorney Docket Number	204552033800

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Examiner Initials*	Cite No.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	37.	WO-94/28204		12-08-1994	Technalum Research, Inc.		
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/Michael Logie/

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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /M.L./

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			Art Unit	2881	
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NON PATENT LITERATURE DOCUMENTS					
Examine r Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T‡
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages			
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages			✓
	52.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages			✓
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	54.	International Search Report, mailed May 7, 2004, directed to International Patent Application No. PCT/JP03/15906; 3 pages			
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/Michael Logie/

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Sheet	3	of	3	Attorney Docket Number	204552033800

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Examiner Signature	/Michael Logie/	Date Considered	04/28/2009
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